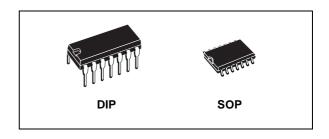


HCF4066B

QUAD BILATERAL SWITCH FOR TRANSMISSION OR MULTIPLEXING OF ANALOG OR DIGITAL SIGNALS

- 15V DIGITAL OR ± 7.5V PEAK TO PEAK SWITCHING
- 125Ω TYPICAL ON RESISTANCE FOR 15V OPERATION
- \blacksquare SWITCH ON RESISTANCE MATCHED TO WITHIN 5Ω TYP. OVER 15V SIGNAL INPUT RANGE
- ON RESISTANCE FLAT OVER FULL PEAK TO PEAK SIGNAL RANGE
- HIGH ON/OFF OUTPUT VOLTAGE RATIO : 65dB TYP. at $f_{IS} = 10$ KHz, $R_{I} = 10$ K Ω
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at f_{IS} = 1KHz, V_{IS} = 5 V_{pp} , V_{DD} V_{SS} ≥ 10V, RL = 10K Ω
- EXTREMELY LOW OFF SWITCH LEAKAGE RESULTING IN VERY LOW OFFSET CURRENT AND HIGH EFFECTIVE OFF RESISTANCE: 10pA TYP.

 at V_{DD} V_{SS} = 10V, T_{amb} = 25°C
- EXTREMELY HIGH CONTROL INPUT IMPEDANCE (control circuit isolated from signal circuit 10¹²Ω typ.)
- LOW CROSSTALK BETWEEN SWITCHES : 50dB Typ. at $f_{IS} = 0.9 MHz, R_{I} = 1 K\Omega$
- MATCHED CONTROL INPUT TO SIGNAL OUTPUT CAPACITANCE : REDUCES OUTPUT SIGNAL TRANSIENTS
- FREQUENCY RESPONSE SWITCH ON: 40MHz (Typ.)
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS



ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4066BEY	
SOP	HCF4066BM1	HCF4066M013TR

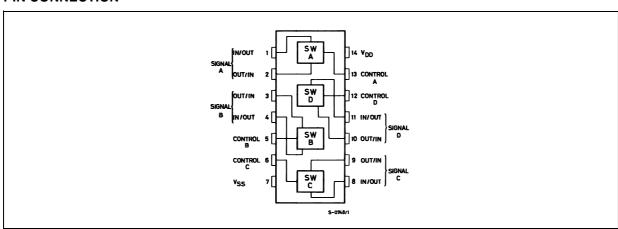
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4066B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4066B is a QUAD BILATERAL SWITCH intended for the transmission or multiplexing of analog or digital signals.

It is pin for pin compatible with HCF4016B, but exhibits a much lower ON resistance. In addition,

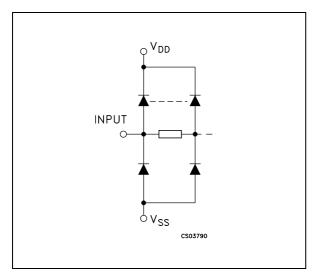
PIN CONNECTION



September 2001 1/9

the ON resistance is relatively constant over the full input signal range. The HCF4066B consists of four independent bilateral switches. A single control signal is required per switch. Both the p and n device in a given switch are biased ON or OFF simultaneously by the control signal. As shown in schematic diagram , the well of the n-channel device on each switch is either tied to the input when the switch is ON or to $V_{\mbox{\footnotesize SS}}$ when the switch is OFF. This configuration eliminates

INPUT EQUIVALENT CIRCUIT



the variation of the switch-transistor threshold voltage with input signal, and thus keeps the ON resistance low over the full operating signal range. The advantages over single channel switches include peak input signal voltage swings equal to the full supply voltage, and more constant ON impedance over the input signal range. For sample and hold applications, however, the HCF4016B is recommended.

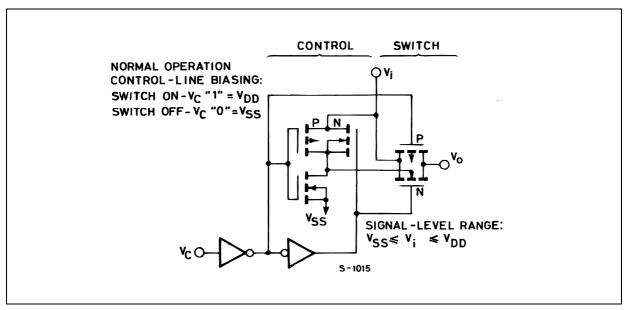
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 8, 11	A to D I/O	Independent Inputs/Outputs
2, 3, 9, 10	A to D O/I	Independent Outputs/ Inputs
13, 5, 6, 12	CONTROL A to D	Enable Inputs
7	V _{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION
Н	ON
L	OFF

 $\begin{array}{l} \textbf{SCHEMATIC DIAGRAM} \text{ (1 OF 4 IDENTICAL SWITCHES AND ITS ASSOCIATED CONTROL} \\ \textbf{CIRCUITY)} \end{array}$



2/9

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

ELECTRICAL CHARACTERISTICS

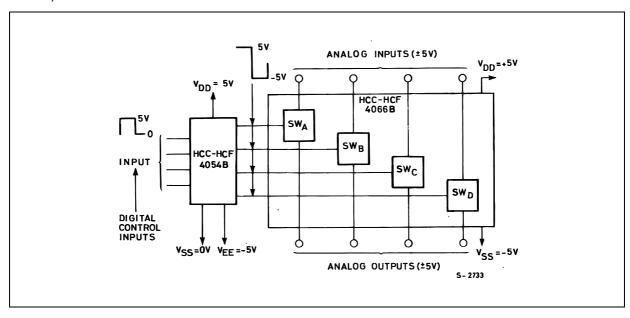
 $(T_{amb} = 25^{\circ}C, Typical temperature coefficient for all V_{DD} value is 0.3 \%/^{\circ}C)$

		Test Co	ndition		Value							
Symbol	Parameter		V _I	V _{DD}	T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
			(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Device		0/5	5		0.01	0.25		7.5		7.5	
	Current (all		0/10	10		0.01	0.5		15		15	μΑ
	switches ON or all switches OFF)		0/15	15		0.01	1		30		30	μΛ
	ownerios si i j		0/20	20		0.02	5		150		150	
SIGNAL	INPUTS (VIS) and C	OUTPUTS (Vos)										
R _{ON}	Resistance	$V_C = V_{DD} R_L =$	10ΚΩ	5		470	1050		1200		1200	
		Return to (V _{DD} -	·V _{SS})/2	10		180	400		500		500	Ω
		$V_{IS} = V_{SS}$ to	V_{DD}	15		125	240		300		300	
Δ_{ON}	Resistance Δ_{RON}			5		5						
	(between any 2 of	$R_L = 10K\Omega, V_C$	$= V_{DD}$	10		10						Ω
	4 switches)			15		15						
TDH	Total Harmonic Distortion	$V_C = V_{DD} = 5V$, $V_{SS} = V_{IS}$ (p-p) = 5V, $R_L = 1$ (sine wave centered in $f_{IS} = 1$ KHz sine way		0KΩ n 0V)		0.4						%
	-3dB Cutoff Frequency (Switch on)	$V_C = V_{DD} = 5^{\circ}$ $V_{IS} (p-p) = 5^{\circ}$ (sine wave ce	V, R _L =	1ΚΩ		40						MHz
	-50dB Feedthrough Frequency (switch off)	$V_C = V_S$ $V_{IS} (p-p) = 5^V$ (sine wave ce	v, R _L =			1						MHz

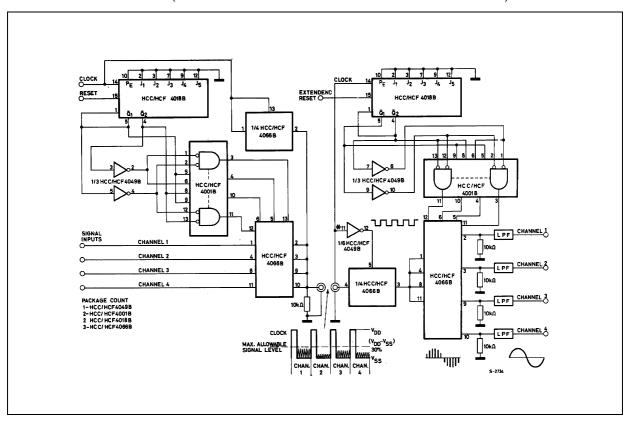
		Test Condition		Value							
Symbol	Parameter	V _I	V _{DD}	Т	_ _A = 25°	С	-40 to 85°C		-55 to 125°C		Unit
		(v)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
	-50dB Crosstalk Frequency	$V_{C(A)} = V_{DD} = +5$ $V_{C(B)} = V_{SS} = -5$ $V_{IS(A)} = 5V (p-p)$ 50Ω source, $R_L = 1$	V		8						MHz
t _{pd}	Propagation Delay	$R_L = 200K\Omega, V_C = V$			20	40					
İ	Time (signal input to output)	$V_{SS} = GND, C_L = 5$	0pF		10	20					
	to duput)	V_{IS} = 10V square wave centered t_r , t_f = 20ns	on 5V		7	15					ns
C _{IS}	Input Capacitance				8						
C _{OS}	Output Capacitance	$V_C = V_{SS} = -5$	+5		8						pF
C _{IOS}	Feedthrough				0.5						
	Input/Output Leakage Current Switch OFF	$V_{C} = 0V$ $V_{IS} = 18V, V_{OS} = 0V$ $V_{IS} = 0V, V_{OS} = 18V$	18		±10 ⁻³	±0.1		±1		±1	μΑ
CONTRO	DL (V _C)		I	ı		I	I	I		·	
V _{ILC}	Control Input Low		5			1		1		1	
	Voltage	I _{IS} < 10 μA	10			2		2		2	V
.,	0	$V_{IS} = V_{SS}, V_{OS} = V_{DD}$	15			2		2		2	
V_{IHC}	Control Input High Voltage	and $V_{IS} = V_{DD}$, $V_{OS} = V_{SS}$	5	3.5			3.5		3.5		.,
	vollago	VIS - VDD, VOS - VSS	10 15	7 11			7 11		7		V
I _I	Input Leakage Current	$V_{IS} \le V_{DD}$ $V_{DD} - V_{SS} = 18V$	18	.,	±10 ⁻⁵	±0.1		±1	11	±1	μΑ
	Crosstalk (control input to signal output)	$V_C = 10V$ (sq. wave) t_r , $t_f = 20$ ns $R_L = 10$ KΩ	10		50						mV
	Turn - On	$V_{IN} = V_{DD} t_r, t_f = 20 ns$	5		35	70					
	Propagation Delay Time	$C_1 = 50 \text{pF}, R_1 = 1 \text{K}\Omega$	10		20	40					ns
			15		15	30					
	Control Input Repetition Rate	$V_{IS}=V_{DD}, V_{SS}=GND$	5		6						
	. topolition Nato	$R_L = 1K\Omega$ to GND $C_L = 50pF, V_C = 10V$	10 15		9.5						
		sq. wave center on 5V t _p , t _f = 20ns V _{OS} =1/2V _{OS} at 1KHz	15		9.5						MHz
Cı	Input Capacitance	Any Input			5	7.5					pF
<u> </u>	par capacitarioc	/iiiy iliput	<u> </u>	<u> </u>		7.5				<u> </u>	Ρı

4/9

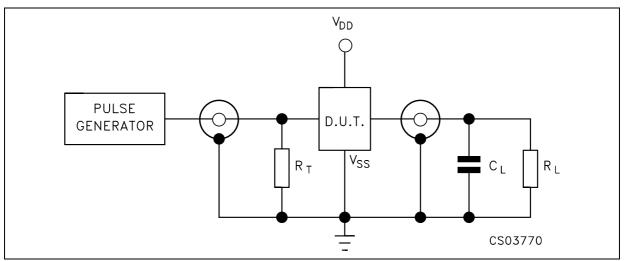
TYPICAL APPLICATIONS (BIDIRECTIONAL SIGNAL TRANSMISSION VIA DIGITAL CONTROL LOGIC)



TYPICAL APPLICATIONS (4-CHANNEL PAM MULTIPLEXER SYSTEM DIAGRAM)

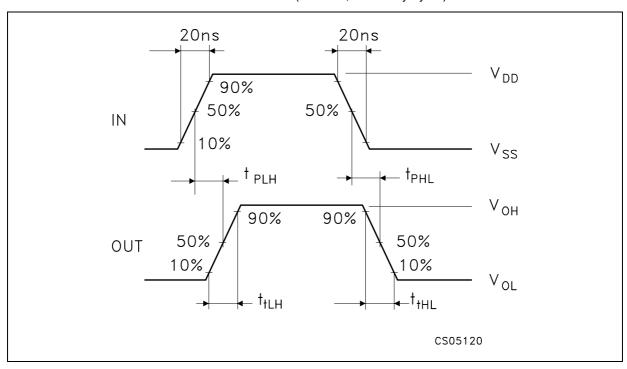


TEST CIRCUIT



 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200KΩ R_T = Z_{OUT} of pulse generator (typically 50Ω)

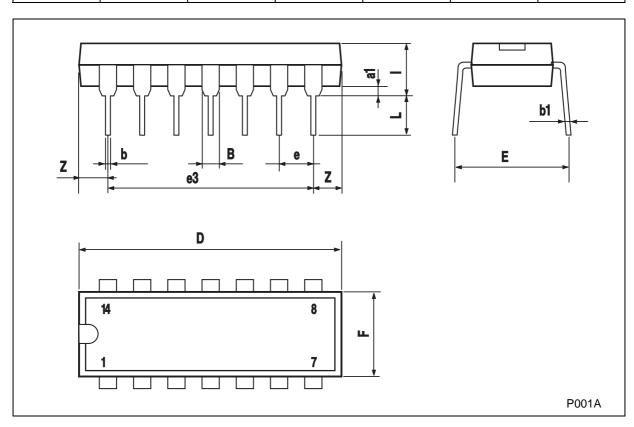
WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



47/ 6/9

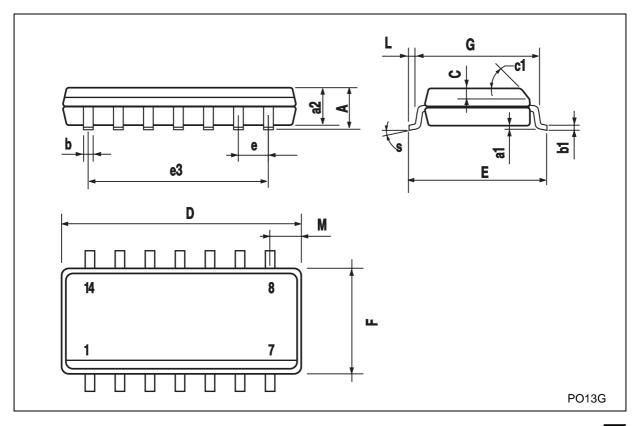
Plastic DIP-14 MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



SO-14 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
Α			1.75			0.068		
a1	0.1		0.2	0.003		0.007		
a2			1.65			0.064		
b	0.35		0.46	0.013		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.019			
c1			45°	(typ.)	•			
D	8.55		8.75	0.336		0.344		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
еЗ		7.62			0.300			
F	3.8		4.0	0.149		0.157		
G	4.6		5.3	0.181		0.208		
L	0.5		1.27	0.019		0.050		
М			0.68			0.026		
S			8° (ı	max.)				



8/9

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